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Dimitris Pavlidis

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DRDA, The University of Michigan

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High layer quality GaN NDR layers have been grown in house by newly set up MOCVD facility. Record quality A1N layers were grown for high thermal conductivity substrateless diodes with improved thermal management. GaN Gunn diodes were designed and fabricated on Si substrates with high thermal conductivity. Combined with the use of small size devices they allowed to bias GaN NDR diodes under electric fields suitable for oscillation. Liquid Nitrogen Characterization of GaN NDR diodes manifested clear increase of current handling as necessary for establishment of NDR conditions. Planar GaN NDR diodes have been investigated as an alternative to vertical designs. InGaN/GaN superlattice designs have been theoretically and experimentally investigated for THz signal generation. Pulse generation setups have been developed to respond to high power, nsec time needs of GaN NDR diodes. On wafer probe techniques with built-in resonators have been investigated for high frequency testing of NDR diodes. Experimental micromachining technology was developed for silicon. Waveguide, probes, transitions and flanges developed and tested in W band. Excellent experimental results were obtained in W band. Nearly finished with corresponding GaAs process technology. Technology demonstration was made with complete W band multiplier.

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Solid State THz Sources



FINAL REPORT

September 23, 2003

The University of Michigan

Dimitris Pavlidis

Professor of EECS

The University of Michigan

Department of Electrical Engineering
and Computer Science

1301 Beal Ave.

Ann Arbor, MI 48109-2122

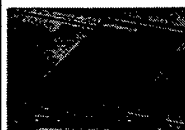
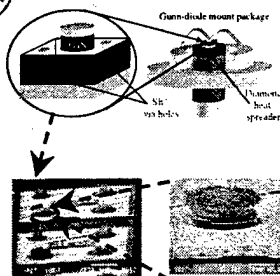
Tel: (734) 647-1778, Fax: (734) 763-9324

e-mail: pavlidis@umich.edu

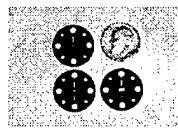
URL: www.eecs.umich.edu/dp-group



GaN Gunn Source Technology



W-band waveguide Transition



Waveguide flanges

Goals, Objectives and Main Technical Approach

Develop solid-state THz sources using GaN NDR (Negative Differential Resistance) diode oscillators and micromachining.

The NDR devices can further be integrated using low-cost power combining networks and cavities operating at Terahertz frequencies.

Silicon micromachining has been selected as the enabling technology of building blocks for circuits and systems at THz frequencies. Micromachining technology is used for the fabrication of scaleable THz structures

Major Impact of Technology and Accomplishments

The use of wide bandgap GaN-based semiconductors is expected to result in increased operating frequency of Gunn-effect enabling for the first time, THz signal generation using solid-state Gunn diode oscillators.

Micromachined structures are low cost alternatives that can batch produce a variety of components needed at submillimeter frequencies. The major impact of this research will be to greatly reduce the cost and development time of THz circuits

GaN Gunn diodes were designed and fabricated on Si substrates with high thermal conductivity. Combined with the use of small size devices they allowed to bias GaN NDR diodes under electric fields suitable for oscillation. Deep RIE technology has been optimized for waveguide and probe fabrication. Initial results show excellent insertion and return loss over W band.

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Program Objective and Strategy



Develop solid-state THz sources using GaN NDR (Negative Differential Resistance) diode oscillators and micromachining..

The NDR devices can further be integrated using low-cost power combining networks and cavities operating at Terahertz frequencies. GaN bulk NDR devices are explored as possible THz sources and other alternatives such as SL and Schottky tunnel designs are evaluated.

Silicon micromachining has been selected as the enabling technology of building blocks for circuits and systems at THz frequencies. Silicon and GaAs technology is used to micromachine THz structures. W band multipliers are used as a proof of concept and extension of the technology to submillimeter wave and THz frequencies is envisaged.

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Technical Challenges



- Transport properties and Negative Differential Resistance Properties of GaN and Nitride-Based Compounds
- Low defect concentration of nitride surfaces exposed to deep etching.
- Efficient thermal dissipation in GaN-based NDR devices
- Substrate removal, packaging and testing of high power GaN NDR devices.
- Combination of micromachined structures with sources
- Process development for DRIE depths deep enough to allow waveguide fabrication
- First demonstration of deep etch technology in GaAs for submillimeter applications
- Design and development of circuit elements limited by technology geometries

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Key Milestones



- High layer quality GaN NDR layers have been grown in house by a newly set up MOCVD facility
- Record quality AlN layers were grown for high thermal conductivity substrateless diodes with improved thermal management.
- GaN Gunn diodes were designed and fabricated on Si substrates with high thermal conductivity. Combined with the use of small size devices they allowed to bias GaN NDR diodes under electric fields suitable for oscillation.
- Liquid Nitrogen Characterization of GaN NDR diodes manifested clear increase of current handling as necessary for establishment of NDR conditions.
- Planar GaN NDR diodes have been investigated as an alternative to vertical designs.
- InGaN/GaN superlattice designs have been theoretically and experimentally investigated for THz signal generation.
- Pulse generation setups have been developed to respond to high power, nsec time needs of GaN NDR diodes. On wafer probe techniques with built-in resonators have been investigated for high frequency testing of NDR diodes.
- First DRIE fabricated waveguides in WR10 and WR3
- Fully micromachined transitions covering full waveguide band in WR10
- Fabrication of state of the art planar monolithic W band multipliers
- GaAs deep etch technology

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Technology Transition/Insertion/Commercialization Plan



- We have established various collaborations with government and industry laboratories for advancing, testing and using the developed technology. This includes manufacturers of Gunn diodes and government/academic laboratories.
- Proposals to NASA Glen and NASA JPL for further work at THz frequencies
- ARO MURI research program to develop low cost sources for chemical and biological sensing applications

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Outline

- Introduction
- THz GaN NDR diode oscillators
- THz Micromachined Structures
- Conclusions

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THz GaN NDR diode oscillators

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Outline

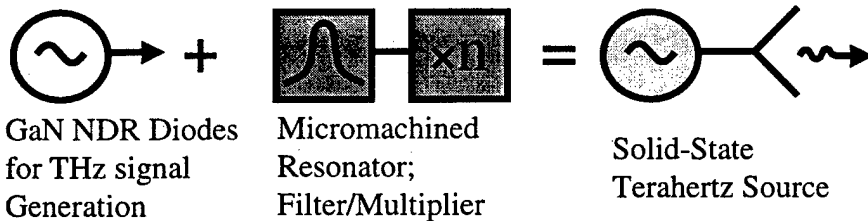


- Introduction
- Operation of GaN NDR diode oscillators
- Development and optimization of fabrication technology
- Fabrication of GaN NDR diodes
- Si wafer thinning technology
- Electrical characterization of NDR diodes
- Packaging and RF testing of GaN NDR diodes
- Conclusions

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Solid-State Terahertz Sources (The UofM Approach)

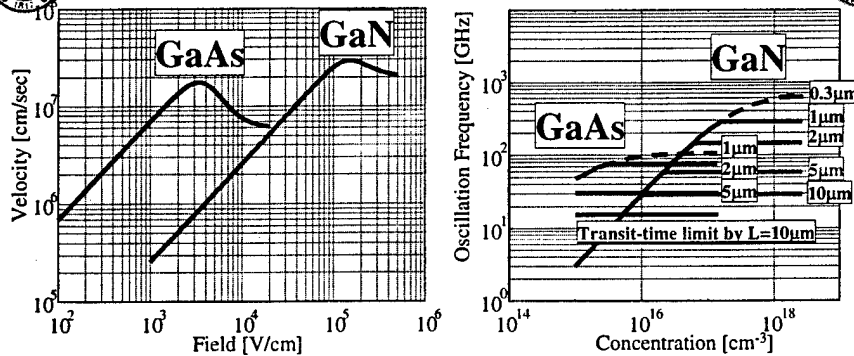


- Unique approach combining new semiconductor and micromachined concepts
- Semiconductor device potential for high-power fundamental or harmonic sources
- Possibility to apply micromachined concept to other sources developed under this program

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Use of GaN for Signal Generation

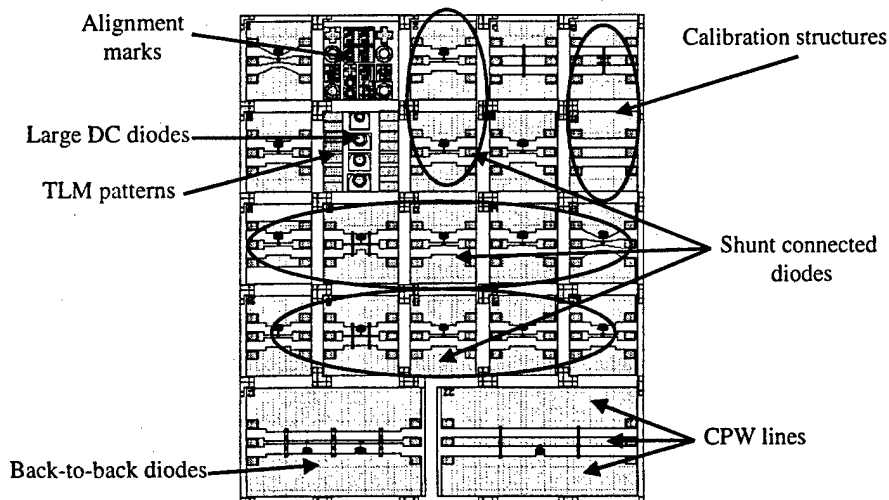


- Theoretical and experimental studies of electron transport in GaN predict critical field $>150\text{KV/cm}$ and peak velocity $>2 \times 10^7\text{cm/s}$
- Maximum frequency of oscillations in NDR devices is limited by the energy-relaxation and intervalley relaxation time.
 - Frequency of GaAs Gunn diodes is limited by electron scattering at $\sim 100\text{GHz}$, while in GaN this limit is at $\sim 800\text{GHz}$

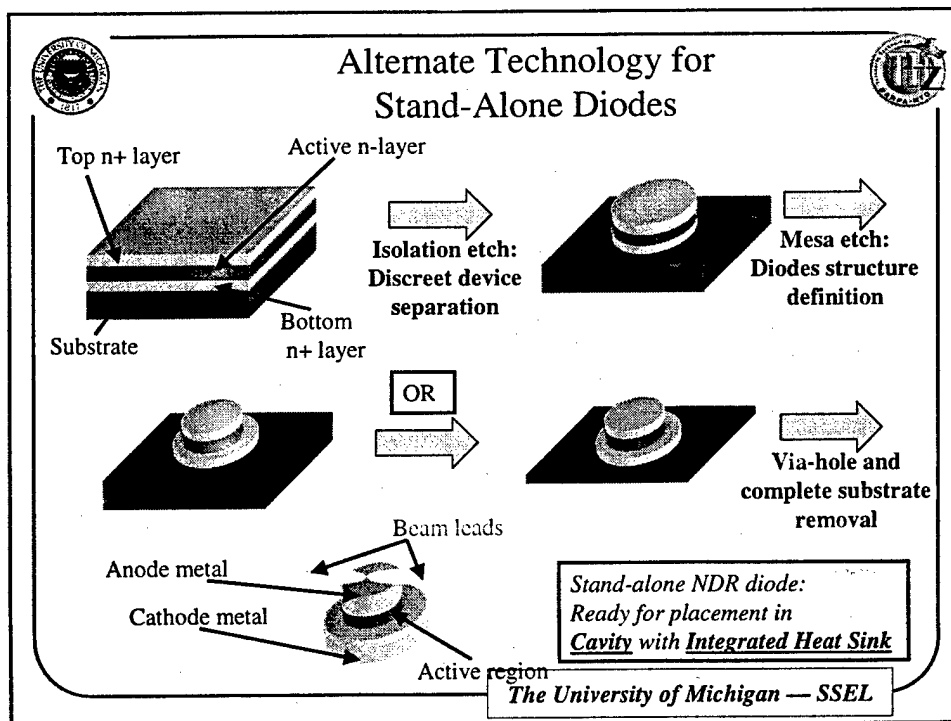
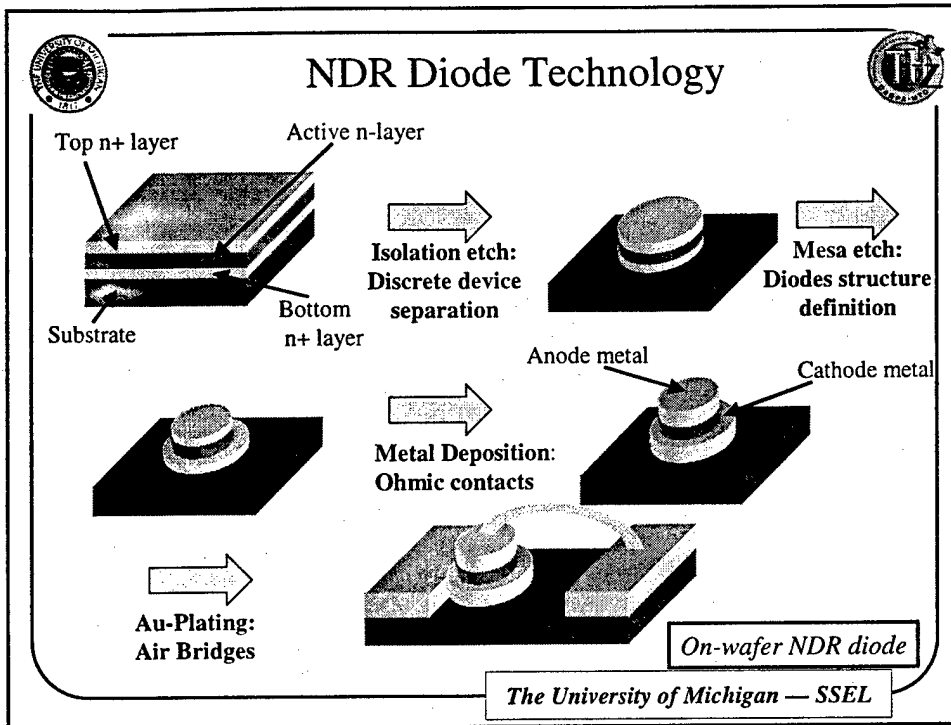
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GaN NDR Diode Fabrication Mask Set for Small Size Diodes

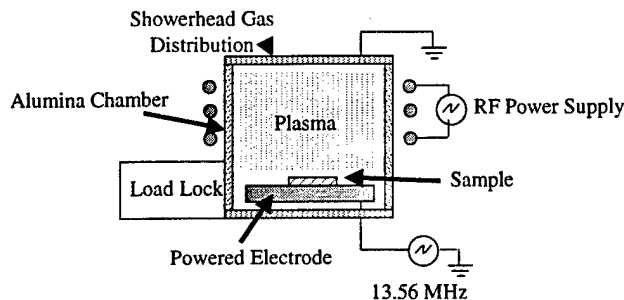


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ICP Etching



- Unlike RIE that uses parallel plate reactor, ICP utilizes inductively coupled plasma
- ICP has several **advantages** over RIE:
 - Operation over wider range of pressures (1 – 500 mTorr)
 - Plasma density increases linear with power up to high power levels
 - ICP can produce more anisotropic etches compared to RIE
 - Plasma is usually more dense leading to chemical etching enhancement
⇒ **Less surface damage**
 - ICP allows better selectivity between the etched and the masking materials

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Etching of GaN:

Sample UMTS125 with 100 nm n+ GaN ($1 \times 10^{19} \text{ cm}^{-3}$) cap layer, 1 micron n- GaN active layer ($1 \times 10^{17} \text{ cm}^{-3}$), 500 nm n+ GaN bottom contact layer ($8 \times 10^{18} \text{ cm}^{-3}$), 1.96 microns u-GaN ($4 \times 10^{16} \text{ cm}^{-3}$) and a 20 nm LT-NL (nucleation layer ?).

Sample description:

A-type: mesa etching with 5 microns thick AZ4562 resist mask (targeted etch depth: about 1300 nm)

B-type: mesa etching with a combination of Ti/Al/Ti/Au-metallization (22nm/78nm/22nm/83nm) and 1.5 microns thick HiPR6517 resist as mask.

Test samples: AZ4562 on glass, the B-structures with and without photoresist on Glass (possibility to determine the etching rate of photoresists and metallisations)

Etching machine: Oxford Instruments Plasmalab 80plus RIE system

Gas: SiCl_4 , 5 sccm

Base pressure: 8×10^{-6} mbar

rf power: 200 W

measured self-bias: between

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Etching procedure: 15 min etching, 10-25 min break for the pressure to recover

Test results: 3x15 min etching + 2x10 min break

etch depth of AZ4562: 1500 nm

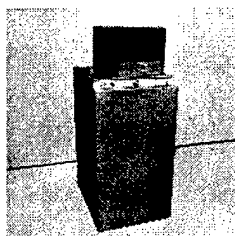
etch depth of glass: 100 nm

etch depth of GaN: 760 nm (17 nm/min)

2d Batch: 76 min etch + breaks, etch depth of GaN: 800nm (11nm/min)

expected etch depth: about 1300nm. Reason: silicide formation slowing down the process.

3d batch to continue the etching, after cleaning of the chamber !!, 15+10+10 min etching and 25+15 min break, etching depth 1600-1700 nm. After cleaning the chamber higher etching rate was observed.

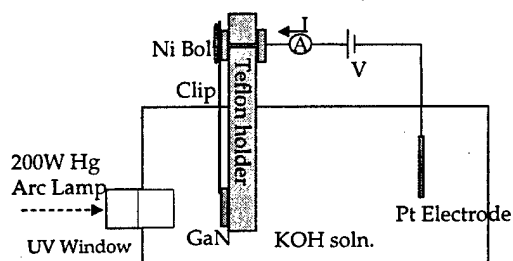


Plasmalab 80Plus for RIE

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PEC Etching of GaN

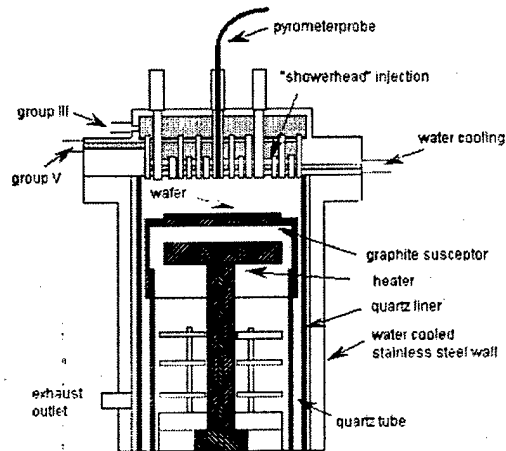


- Etching of GaN occurs due to Photo-electro-chemical reaction at sample surface
 - Arc lamp induces photo-generated e-h pairs in GaN
 - Excitation provided by newly acquired 200W Oriel Hg arc lamp
 - Photo-generated holes assist Redox reaction in KOH solution
 - KOH etches the oxidized gallium products
 - HgXe bulb produces a smooth and uniform etch compared with Hg. Etch rate also is different. Rate was Hg) 67 nm/min and HgXe) 150 nm/min.
- Parameter Space for PEC etching
 - Sample Carrier Conc.
 - UV light intensity
 - Solution type
 - Solution conc.
 - Temp.
 - Agitation

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Thomas Swan 3x2" CCS Reactor

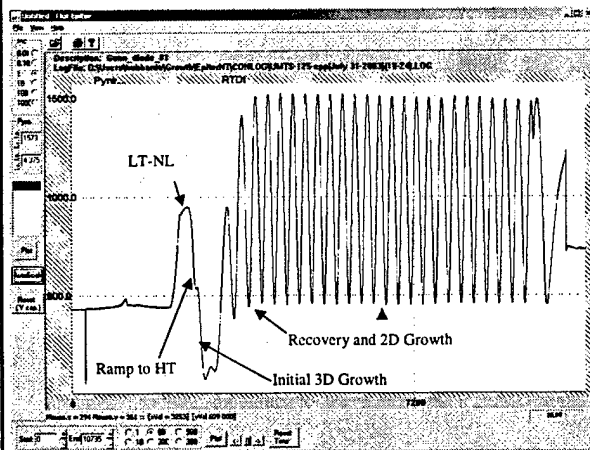


- Vertical GaN Reactor
- Water cooled stainless steel outer chamber
- Quartz inner chamber
- Rotating susceptor to improve uniformity
- "Showerhead" injection for efficient gas delivery and mixing
- 3-zone heater for uniform temperature distribution
- Dry Nitrogen purged glovebox enclosure

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Interferometer Trace

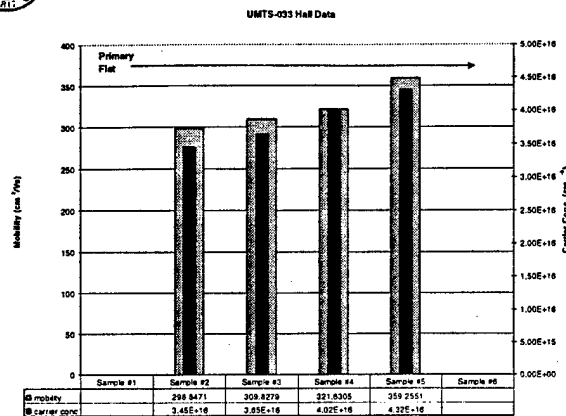


- Interferometer trace shows smooth LT GaN growth then subsequent roughening during the ramp to 1040C.
- After ~1200 sec of 3D growth, HT GaN material is recovered and growing with smooth surface and constant growth rate
- Growth Rate ~ 1.7 $\mu\text{m/hr}$, consistent with XSEM

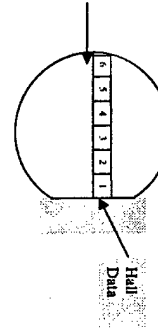
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UID Hall Results



Cleave
for SEM



- Cut 6 300x300 mil (7.5x7.5 mm²) square for Hall
- Background doping reduced to $\sim 4 \times 10^{16} \text{ cm}^{-3}$ with corresponding mobility of $\sim 300 \text{ cm}^2/\text{Vs}$.
- Background and mobility appear uniform across the wafer.

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Gunn Diode Structures



100 nm n ⁺ -GaN contact (1e19 cm ⁻³)
1 μm n ⁺ -GaN contact (1e17 cm ⁻³)
500 nm n ⁺ -GaN contact (8e18 cm ⁻³)
2 μm UID HT-GaN
LT-GaN NL
400 μm Sapphire

1 μm vertical

100 nm n ⁺ -GaN contact (1e19 cm ⁻³)
2 μm n ⁺ -GaN contact (1e17 cm ⁻³)
500 nm n ⁺ -GaN contact (8e18 cm ⁻³)
2 μm UID HT-GaN
LT-GaN NL
400 μm Sapphire

2 μm vertical

100 nm n ⁺ -GaN contact (1e19 cm ⁻³)
3 μm n ⁺ -GaN contact (1e17 cm ⁻³)
2 μm UID HT-GaN
LT-GaN NL
400 μm Sapphire

3 μm planar

- Calibration of doping for silane flows of 4 sccm = $1.0 \times 10^{19} \text{ cm}^{-3}$ and 0.05 sccm = $1.2 \times 10^{17} \text{ cm}^{-3}$. Curve was generated and silane flow calculated for doping of 1×10^{17} , 8×10^{18} , and $1 \times 10^{19} \text{ cm}^{-3}$.
- Growth of three Gunn diode structure. Sample 125 is traditional vertical structure with 1 μm active layer. Sample 126 is vertical but with a 2 μm active layer. Sample 128 is a planar Gunn structure with a 3 μm active layer.

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Suppression of Yellow luminescence deep centers of GaN

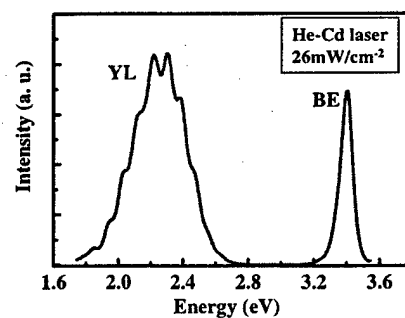


- **Yellow luminescence center:** a universal feature of GaN located around 2.3 eV.
- **YL source:** electrons from conduction band or a shallow donor to a deep state.
- **Deep state:** Ga vacancy or complex of Ga vacancy with impurity.
- **Effects:** YL centers may influence GaN based device performance
→ high quality GaN layers evidenced by small FWHM/XRC, low noise and large carrier lifetime constants are associated with small YL.
- Use YL to optimize GaN device quality.

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RT Photoluminescence of GaN

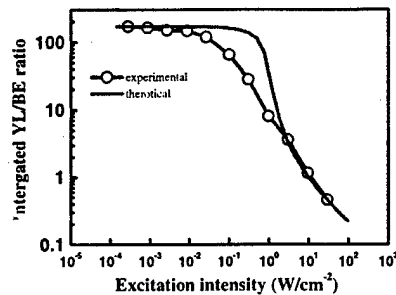


Typical PL shows a narrow band edge (BE) peak (~3.4 eV) and broad yellow luminescence (YL) band (~2.3 eV).

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Integrated Yellow to Band edge Luminescence (YL/BE) ratio

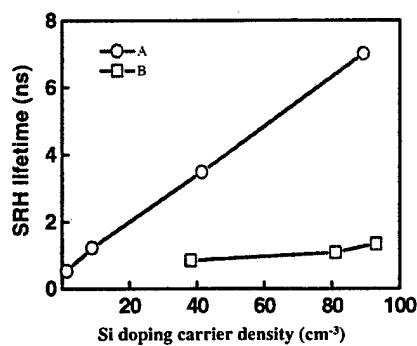


- The experimental data and Shockley-Read -Hall Model calculation agree well at low and high excitation density.
- SRH lifetime can be extracted from low excitation region (1.25 ns).

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YL of Si doped GaN



At low excitation density:

$$1/\tau_{SRH} = \sigma_p v_{th} N_t = (YL/BE) \cdot B \cdot N_d$$

$B = 4.7 \times 10^{-11} \text{ cm}^3/\text{s}$ (Constant related to band-to-band recombination)

Buffer layer growth conditions were changed to study impact on Si-GaN quality

group	Growth time (s)	Ramp time (s)	Re-crystalline time (s)
A	230	300	60
B	200	300	150

(002) FWHM-XRD_A ~ 300", FWHM-XRD_B ~ 360".

- SRH lifetime of YL centers can be extracted using Hall carrier density N_d and YL to BE ratio.
- The lifetime of YL increases nearly linearly with Si doping density.
- Si substitutes the deep-level Ga vacancy → formation of shallow donor levels decreases YL band (deep level density) → improved material quality ($\tau_{SRH} \uparrow$).
- Si-GaN lifetime increases for high quality buffer layer A.

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Growth Pressure and V/III Ratio Effects YL Deep Center

sample	Si doped Carrier density (cm ⁻³)	V/III ratio	Pressure (Torr)	SRH lifetime (ns)
A	3.73×10^{18}	1400	100	0.34
B	4.33×10^{18}	800	100	0.15
C	8.93×10^{18}	1000	200	7.0
D	8.43×10^{18}	1000	100	0.75

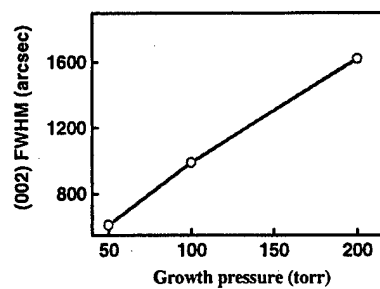
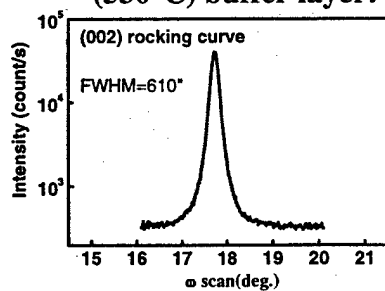
- High V/III ratio suppresses the Ga vacancy $\rightarrow YL \downarrow \rightarrow \tau_{SRH} \uparrow$
- Increase of reactor pressure also reduces V/III ratio $\rightarrow YL \downarrow \rightarrow \tau_{SRH} \uparrow$
- SRH lifetime is good indication for growth optimization.
(high V/III and high pressure needed for improved GaN layer quality)

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High Quality AlN Growth by MOCVD on Sapphire

1. Growth of AlN (0.4~1 μm) on low temperature (530°C) buffer layer:

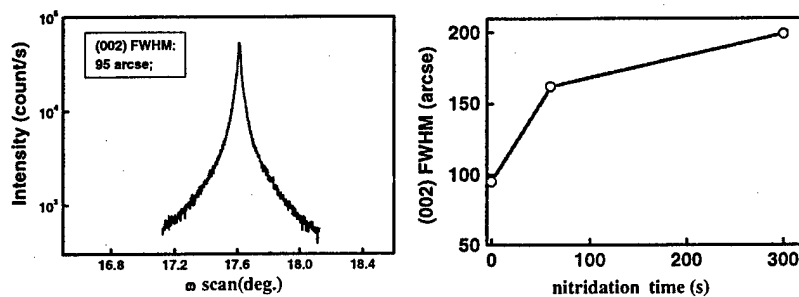


- FWHM-XRD increases with growth pressure.
- AlN layer quality is not acceptable (min. FWHM=610°) if AlN is grown on sapphire using LT-buffer; Same feature expected using LT-GaN buffer.

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2. Direct growth of AlN on sapphire:

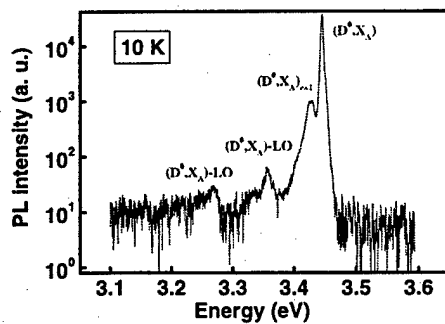


- High quality AlN (0.4 μm) layer was grown on sapphire.
- X-ray rocking curve with excellent FWHM value of 95 arcsec.
- FWHM of x-ray rocking curve is strongly dependent on nitridation time

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Low Temperature PL of GaN Layers Used in NDR-Diodes

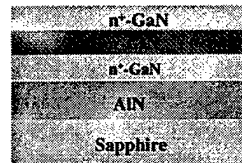


- The main peak is neutral donor bound exciton with FWHM=10 meV.
- Two electron transitions $(D^0, X_A)_{n=2}$; One phonon and two phonon replica were observed.
- The above features indicate high quality samples.

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NDR-GaN Diodes Using AlN for Substrateless Design

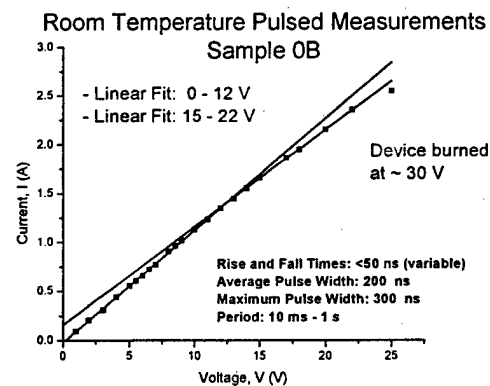


- The obtained high quality AlN could be used as base for growth of substrateless NDR-GaN Diodes → improved handling of thermal issues.
- Growth of high quality GaN-diode layers on AlN buffer would require following studies for reduced AlN surface roughness.
 - ALE-like initial AlN growth on sapphire with excess NH_3 flow for reduced layer roughness.
 - Growth of low XRD FWHM bulk AlN using reduced NH_3 flow.

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Sample 0B Measurement Results



- RT pulsed IV measurements were performed under following pulse conditions:
 - period: >10 ms; rise/fall time: <50 ns; width: 200 ns; max width: <300 ns
- Slight current saturation begins to onset at > 20 V (100 kV/cm)
- After a sudden spike at ~30 V device is burned and left open.

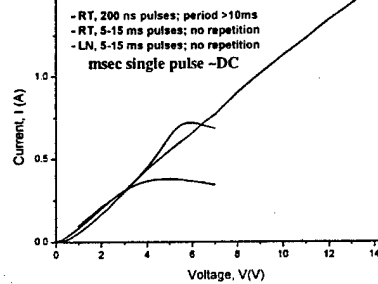
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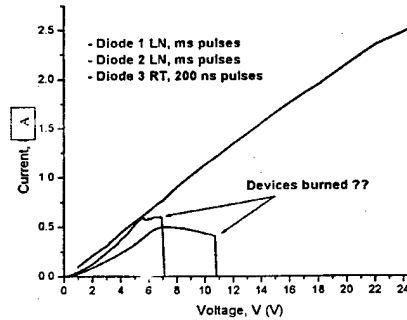
Measurements Under Different Pulse Conditions



Sample 0B: pulsed measurements under different pulse conditions



Sample 0B LN2 tests

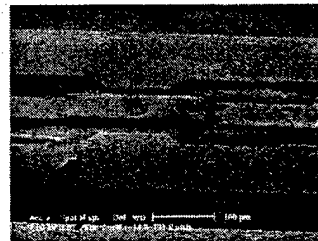
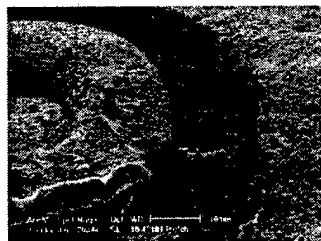
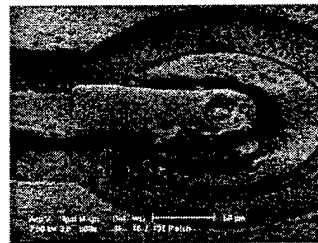
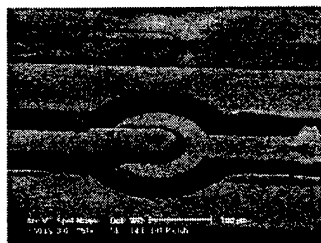


- RT measurements under long pulse conditions ($\sim 300 \mu\text{s}$) showed saturation at $\sim 300 \text{ mA}$
- Same measurement but at LN2 temperature demonstrated higher peak current at $\sim 600 \text{ mA}$ and more pronounced NDR
- Under short pulse conditions (pulse width $\sim 200 \text{ ns}$) current begins to saturate at $\sim 24 \text{ V}$ corresponding to 120 kV/cm even at room temperature

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SEM of the Tested Diodes

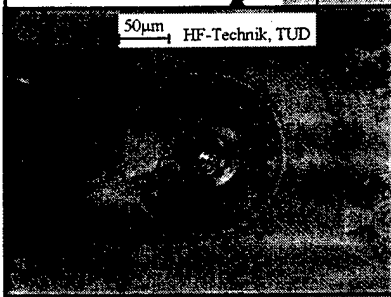
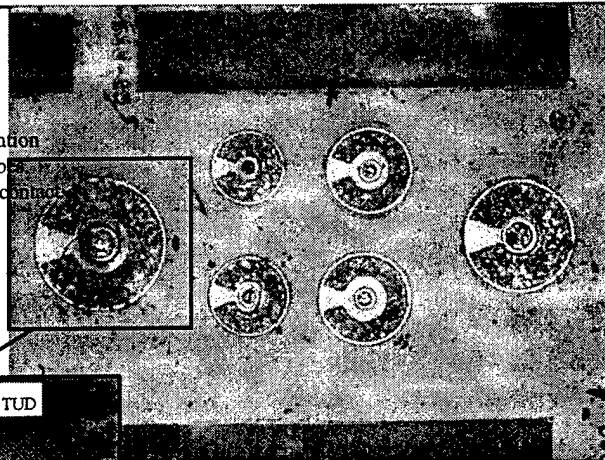


- Anode contacts burn at high fields

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Measured Test Structures of 00B1. The cathode metallisation is not wide enough for the probe. After some measurements the contact deteriorate.



Measured Test Structures of 00B1

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Diodes Mounted on Diamond Heat Sink



Diamond heat sink Thinned and diced diode



Mounted diode (side view)

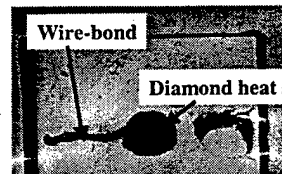


Mounted diode (top view)

Cathode wire-bonded to mount metal



Mounted diode with wire-bonded cathode (side view)



Mounted diode with wire-bonded cathode (top view)

- Collaboration with Quinstar
- Mounting with diamond heat sink improves heat dissipation
⇒ reduction of thermal limitation

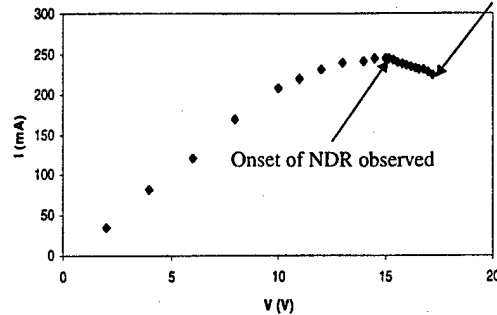
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DC Characteristics of Small Gunn Diodes



Sample MICH 01106-1A. Diode diameter: $\sim 15 \mu\text{m}$ Device burned

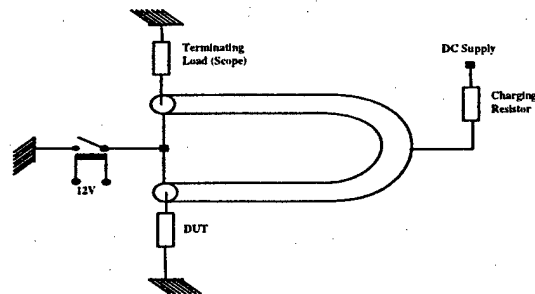


- Previous measurements of GaN on SiC Gunn diodes with $\sim 50\text{-}100 \mu\text{m}$ diameter showed onset of NDR at $V \sim 12\text{V}$ ($E_c \sim 24 \text{ kV/cm}$) with dissipated power $\sim 3\text{-}4\text{W}$
- The critical field for GaN on SiC diodes is well below the predicted values for GaN. NDR effect is severely affected by thermal issues.
- Smaller thickness, $0.5 \mu\text{m}$, diodes on Si have better heat dissipation through the substrate. Possibility to observe NDR effects which are less affected by thermal issues.
- Onset of NDR was observed at $\sim 15\text{-}16\text{V}$
- Corresponding value of the critical field, $E_c \sim 300 \text{ kV/cm}$

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Charged line configuration (Blumlein) for pulse generation

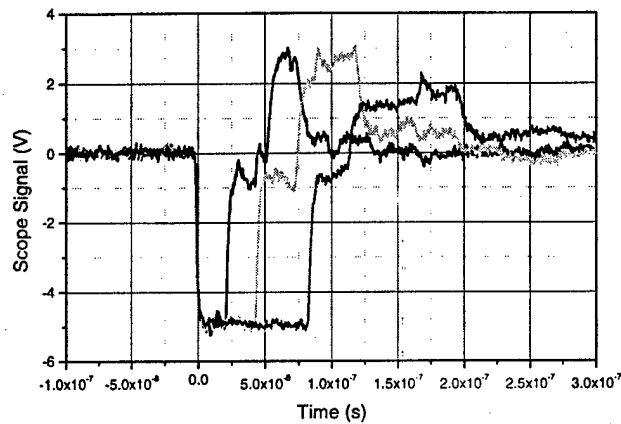


The DC supply V_{ch} is varied between 2 and 500V. The switch is triggered with a period of 100 ms and the trigger pulse of 12V amplitude and 10 ms width (possible to go down to 10 and 2 ms for the period and the width, respectively) is provided by the 8114A pulse generator. The scope is a 50 Ohm terminating load. With a 50 Ohm DUT the scope waveform is a pulse of negative polarity and $V_{ch}/2$ amplitude.

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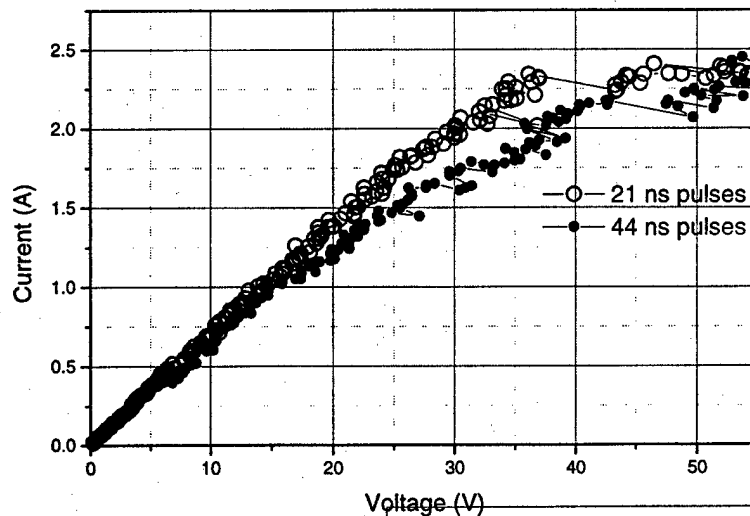
Pulse waveforms with connected diode (00B1) for different pulse widths. The reflected amplitude of the 88 ns pulse is too low, possibly due to poor contacts. There is a 20db atten. Before the scope (max input rms 5V). A factor 10 is to be considered for the voltage scale. The input impedance of the scope is set to 50 Ohm. Pulse waveform @ 100V charge voltage, for 21, 44 and 84 ns pulse width.



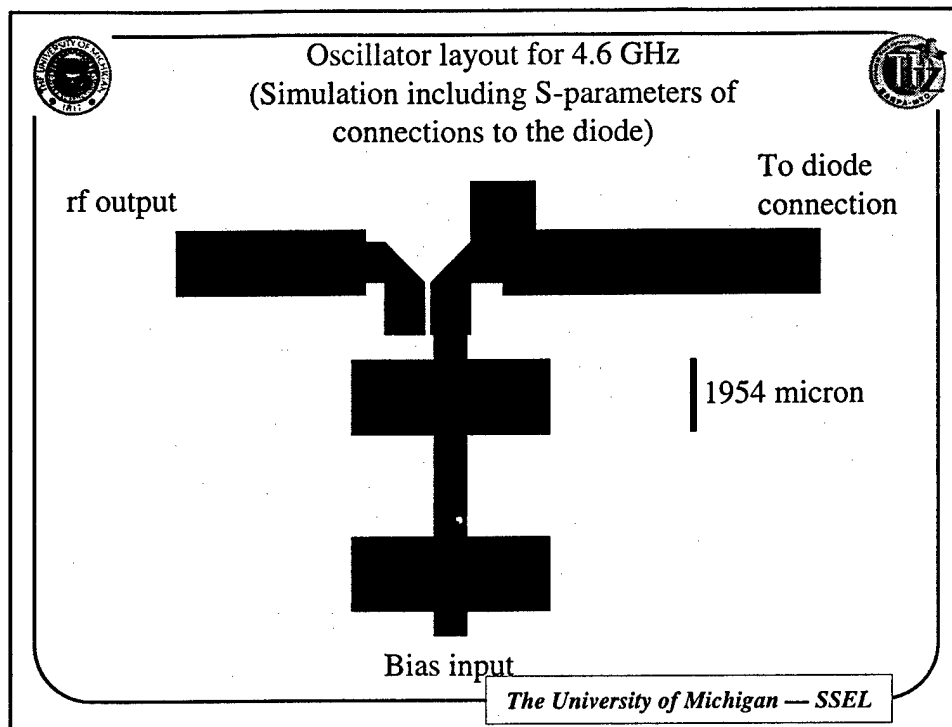
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I-V curves of the 00B1 structures (2 micron thick layer) for 2 pulse widths



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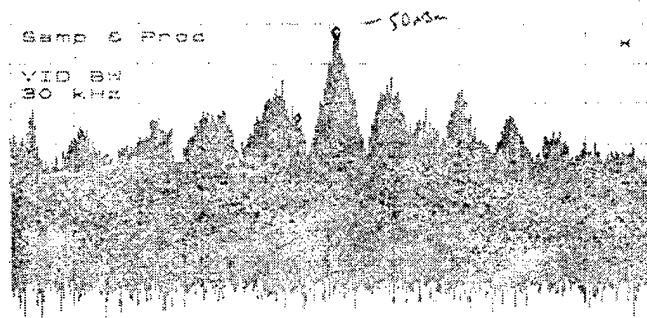
Spectrum analysis of a GaAs Gunn Diode with a resonator



ATTEN 10dB MKR -79.83dBm
RL -40.00dBm 10dB/ 3.9006Hz

Samp 5 Prod

VID BW
30 KHz



6.5V
1.7µsec
Am Band
2µsec

CENTER 3.9006Hz SPAN 1.0006Hz
MARK 100Hz XREF 100Hz SWP 25.0000

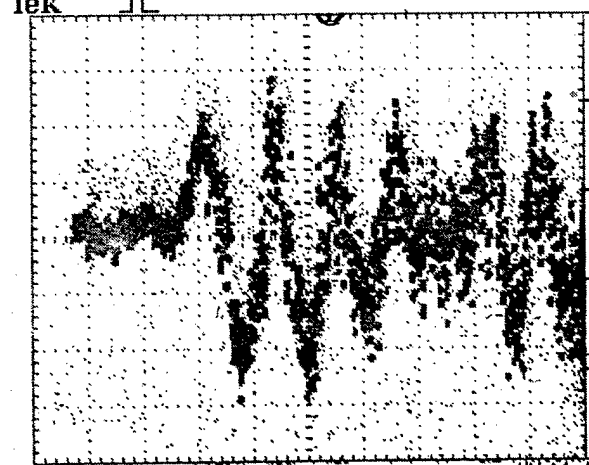
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Sampling-Oscilloscope measurement of a GaAs Gunn Diode with a resonator

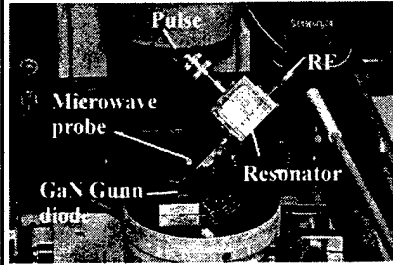


Tek

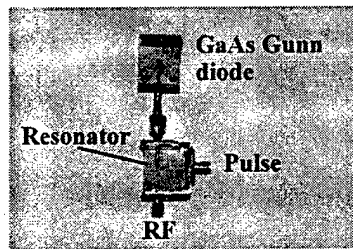


CH1 100mV CH2 50.0mV XY Mode

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On-wafer measurement setup for Gunn oscillations in GaAs and GaN diodes



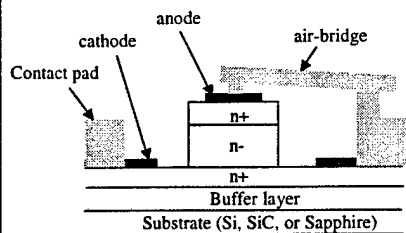
Setup for GaAs Gunn-diode testing (10 microns active layer, 150x200 sq. Microns area, Oscillations at 3.9GHz with 200 ns pulses and 100 us repetition rate.

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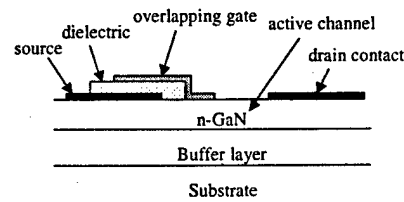
GaN NDR Diode Fabrication

Vertical NDR Structure



- Non-planar approach
- Good thermal dissipation
- Substrate thinning
- ⇒ Integrated heat sink

Horizontal NDR Structure



- Easy integration
- Reduced heat dissipation

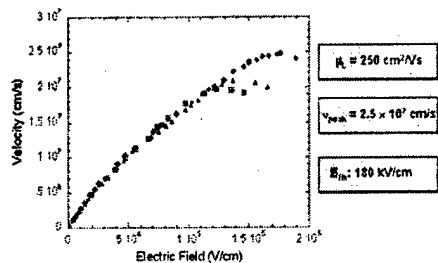
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v-F Measurements



Velocity – Field Measurement Results



J. M. Barker, R. Aziz, D. V. Ferry, S.M. Goodnick, T. J. Thornton, D. D. Koleske, A.E. Wickenden, and R. L. Henry, High Field Transport Studies of GaAs, Physics B 314 29-41 (2002)

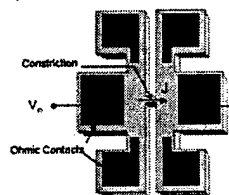
Drift Velocity Measurement

Conductivity Technique (Pulsed IV)

- Measures Current Density as it varies with Electric Field

$$E = \frac{V}{L}$$

$$J(E) = ne\mu_d(E)$$

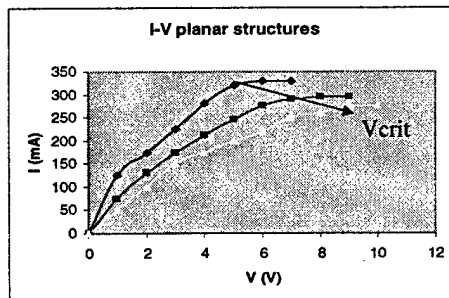


- Velocity saturation is revealed but no real overshoot prior to breakdown ($E_b \sim 180 \text{ kV/cm}$)
- Test structures burned even under pulsed conditions ($t_{\text{pulse}} = 200 \text{ ns}$)
- Breakdown is likely due to localized high field in the constriction ($< 10 \mu\text{m}$)
- Breakdown field is reduced to $< 50 \text{ kV/cm}$ without passivation
- Transport is along a-axis vs. c-axis in our diode design

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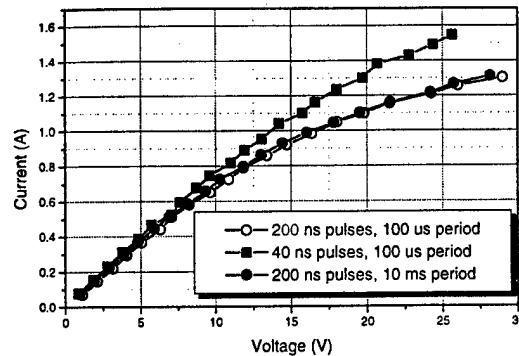


Planar Diode Measurements



- DC measurements of planar TLM-like structures for 3 (black), 6 (purple), 10 (yellow) μm spacing between pads
- The critical voltage is dependent on the diode length; increases with separation

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Measurements with planar structures:

3 microns spacing, 40 ns and 200 ns pulses. Saturation tendency, probably due to thermal effects, reached at lower voltage and current for longer pulses independent of the repetition rate. Saturation field about half of corresponding vertical structures (with 2 microns active layer). Beyond 25V important heat development leading to non reproducible results (shift of the saturation current and voltage to lower values), and destruction of the contact metallization.

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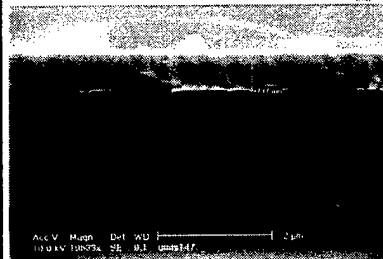


AlGaIn Calibration



750 nm AlGaIn
~ 500 nm u-GaN transition layer
2 μm UID HT-GaN
LT-GaN NL
400 μm Sapphire

Temp	1040C
Time	3000 sec
Pressure	100 Torr
Al flow	43 sccm
Ga flow	20 sccm
[Al]/[Al]+[Ga]	25%
NH3 flow	2500 sccm
Growth Rate	0.9 μm/hr

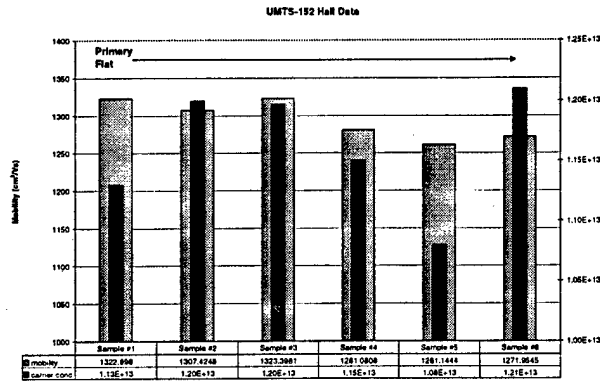


- The TMGa and TMAI flows were selected to give a molar ratio of ~25% Al content. A thick AlGaIn layer was grown to facilitate XRD and X-SEM measurements
- Optical micrograph shows AlGaIn is cracking due to lattice mismatch induced strain in the thick layer .. This is typical for AlGaIn grown direct on GaN.
- X-SEM
 - Cross-Section shows AlGaIn/GaN interface very clearly. Growth rate was determined to be ~0.9 μm/hr.

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AlGaIn/GaN Uniformity

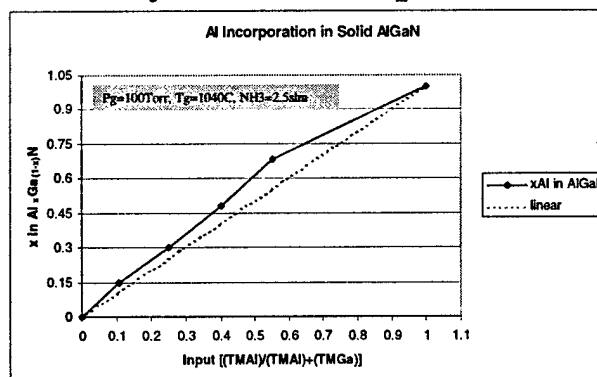


- Mobility and sheet charge are uniform across the wafer
 - Mobility uniformity less than 5%
 - Charge uniformity less than 10%

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Study of Al Incorporation



- Al incorporation into solid AlGaIn shows a super-linear trend
 - We expect reduced Al-NH₃ Pre-reactions due to use of low pressure, low ammonia flow, and close-coupled showerhead reactor design
 - In absence of pre-reaction, quasi-thermodynamic models predict preferential Al incorporation when using high growth temperature and low V/III ratio.
- To verify our data, we are currently studying Al incorporation under various other growth temperature and V/III ratio.

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InGaN Calibration



InGaN 730-750C
~ 350 nm HT-GaN transition layer
2 μ m UID HT-GaN Template (Run#9)
~20-30 nm LT-GaN N.L.
400 μ m Sapphire

Material	InGaN#1 (#51)	InGaN#2 (#54)	Low Temp. GaN
Growth Temp	730°C	750°C	730-750 °C
Carrier Gas	N ₂	N ₂	N ₂
{TMIn}/([TMIn]+[TM Ga])	0.86	0.86	0
Growth Rate	40 nm/hr	80 nm/hr	40-80 nm/hr
XRD-In content	21%	17%	-
NH3	2.5 slm	2.5 slm	2.5 slm
Growth Pressure	200-500 Torr	200-500 Torr	200 Torr

- Thick InGaN was grown directly on GaN to determine growth rate, In content, and layer quality.
 - In content not sensitive to input gas ratio due to In volatility temperature above 500 °C
 - Must change growth temperature or pressure to tune the In content
- LT-GaN also optimized for use in FET to avoid change of growth temperature that could lead to interface degradation

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InGaN/GaN SL Growth for Negative Differential Resistance



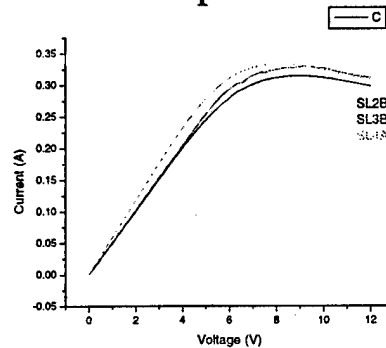
SL #1: without n-GaN caps			SL #2: with n-GaN caps			SL #3: without n-InGaN						
x10	10 nm n-InGaN (~4e18cm ⁻³)	x10	50 nm HT n-GaN (~4e18cm ⁻³)	x10	x10	50 nm HT n-GaN (~4e18cm ⁻³)	x10	x10				
	2.5 nm u-InGaN (~1e17cm ⁻³)		2.5 nm n-GaN (~4e18cm ⁻³)			2.5 nm u-GaN (~1e17cm ⁻³)						
	2.5 nm GaN barrier		10 nm n-InGaN (~4e18cm ⁻³)			2.5 nm u-InGaN (~1e17cm ⁻³)						
	2.5 nm u-InGaN (~1e17cm ⁻³)		2.5 nm u-InGaN (~1e17cm ⁻³)			2.5 nm u-GaN (~1e17cm ⁻³)						
	160 nm n-InGaN (~4e18cm ⁻³)		2.5 nm u-GaN (~1e17cm ⁻³)			500 nm n-GaN (~4e18cm ⁻³)						
~ 500 nm u-GaN transition layer			2.5 nm u-InGaN (~1e17cm ⁻³)	500 nm u-GaN transition layer			500 nm u-GaN transition layer					
2 μm UID HT-GaN Template (Run#9)			40 nm n-InGaN (~4e18cm ⁻³)	2 μm UID HT-GaN Template (Run#9)			2 μm UID HT-GaN Template (Run#9)					
LT-GaN N.L.			500 nm n-GaN (~4e18cm ⁻³)	LT-GaN N.L.			LT-GaN N.L.					
400 μm Sapphire			500 nm u-GaN transition layer	400 μm Sapphire			400 μm Sapphire					

Nominal In concentration for all InGaN layers ~ 5%

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Characterization of InGaN/GaN superlattices



- The I-V characteristic for different structures
- SL2: 10 QWs InGaN/GaN; SL3: 10 QWs GaN/InGaN; SL4: same as SL3 high In%
- All samples processed in parallel and annealed at 750 C

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Breakdown Mechanism



A possible breakdown mechanism between n+ and n- layers is of concern:

Apart from a soft recovery, it is necessary that the diode can withstand a high dI/dt , which may result in dynamic avalanche well below the static breakdown voltage. Dynamic avalanche is caused by a current controlled increase of the effective doping level N_{eff} [see Eq. (1)]. J_p is the hole and J_N the electron current density, v_{sat} the carrier saturation velocity, and N_D the n -base doping.

$$N_{eff} = N_D + \frac{J_p - J_N}{q \times v_{sat}} \quad (1)$$

Diode destruction by dynamic avalanche during reverse recovery has been reported in Refs. 1-3, but a considerably

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Ohmic Contact Considerations



- At high power the Ti/Al/Au ohmic contacts suffer from severe degradation
- First the contact metal begins to melt around the perimeter of the contacts
- When pushed higher in power the top Au "shoots" across the separation between anode and cathode, eventually violently burning the diode under test
- To remedy this problem a new metallization scheme was used:
 - Ti/Al/Ni/Au contacts were used in recent runs
 - Ni serves as a barrier preventing Au from diffusing into the Ti/Al/GaN contact
 - 10-100 times better quality contacts were achieved ($R_{sc} = 4.4 \times 10^{-6} \text{ Ohm/cm}^2$; previous $R_{sc} = 1.3 \times 10^{-4} \text{ Ohm/cm}^2$)
- However, at high powers the top Au layer still melts destroying the diode as described above
- Another approach is currently being tested with introduction of refractory metals into the ohmic metallization scheme (Mo, Pt, W, etc.)
- Although refractory metal contacts have usually higher resistance compared with Ti/Al contacts their power handling capability is much higher

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Conclusions I



- High layer quality GaN NDR layers have been grown in house by a newly set up MOCVD facility
- Record quality AlN layers were grown for high thermal conductivity substrateless diodes with improved thermal management.
- GaN Gunn diodes were designed and fabricated on Si substrates with high thermal conductivity. Combined with the use of small size devices they allowed to bias GaN NDR diodes under electric fields suitable for oscillation.
- Liquid Nitrogen Characterization of GaN NDR diodes manifested clear increase of current handling as necessary for establishment of NDR conditions.
- Planar GaN NDR diodes have been investigated as an alternative to vertical designs.

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Conclusions II



- InGaN/GaN superlattice designs have been theoretically and experimentally investigated for THz signal generation.
- Pulse generation setups have been developed to respond to high power, nsec time needs of GaN NDR diodes. On wafer probe techniques with built-in resonators have been investigated for high frequency testing of NDR diodes.

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THz Micromachined Structures



Yongshik Lee, Jack East and Linda Katehi
The University of Michigan

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Outline

- Overview & Background
- Thz micromachined structures
- Summary

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THz Micromachined Structures

- Goal is to develop silicon and GaAs micromaching technology
- The resulting processes can be used to realize low cost batch fabricated structures from 100 GHz to several THz
- Probes, waveguides, transitions and flanges have been developed and tested
- Continuing efforts will focus on WR10, Wr5 and WR3 circuits and systems

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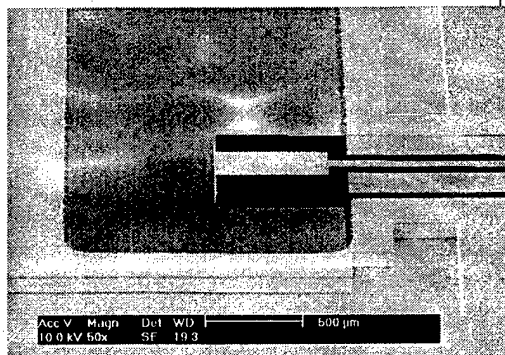


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Deep RIE (DRIE) Technology

- Goal is to realize micromachined elements that can be scaled to THz frequencies
- Design based on HFSS
- Technology based on conventional lithography and a STS deep etch tool
- Example WR 10 waveguide and transition



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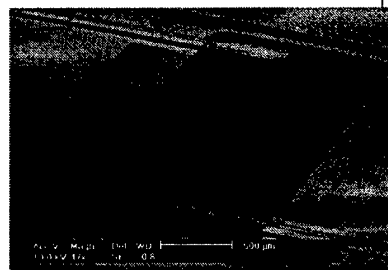


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DRIE (continued)

- Complex structures such as coupling probes positioned with integral backshorts can be fabricated
- Excellent control of dimensions possible
- Assembly and alignment will be critical at higher frequencies
- Batch techniques will be needed to reduce cost



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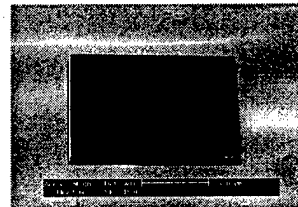
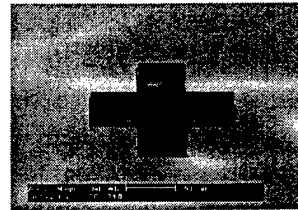


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DRIE (continued)

- Assembly and alignment will be critical at higher frequencies
- Batch techniques will be needed to reduce cost
- Alignment “pins” and “holes” can be easily included as part of the design



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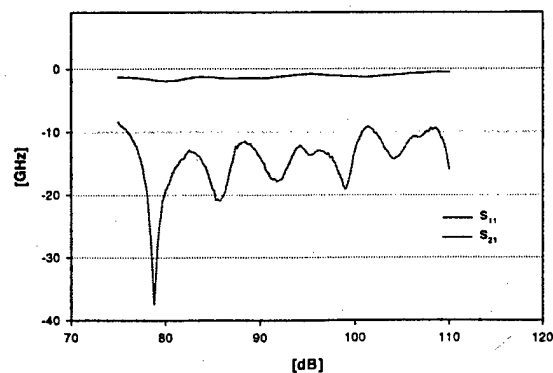


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Transition Results

FGC-to-DRIE Waveguide Transition



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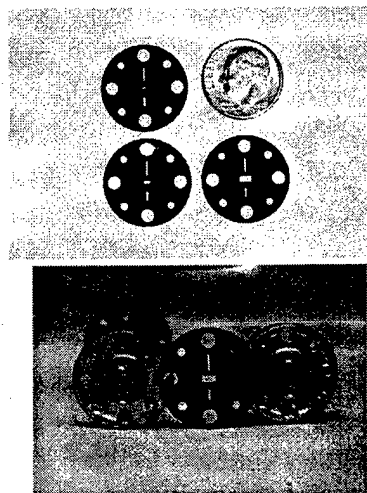


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Waveguide Transitions

- We also need transitions to external waveguide assemblies
- Batch fabrication and accurate low cost alignment and assembly will be critical



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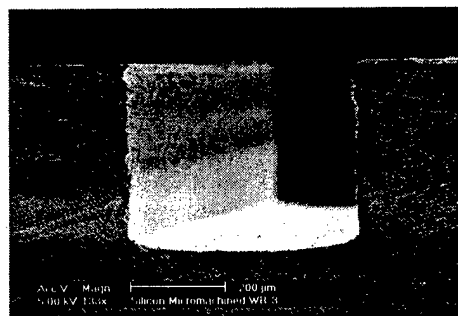


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WR3 DRIE Waveguides

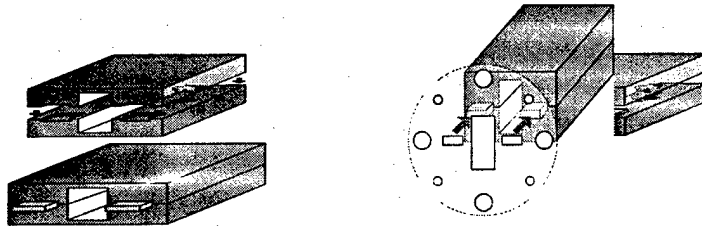
- Nearly vertical walls with slightly curved bottom
- Excellent cross section dimensional control
- Initial surface roughness reasonable, can be improved with slower etching and oxidation smoothing
- CST analysis shows excellent return loss with expected misalignment



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Flange Alignment & Assembly



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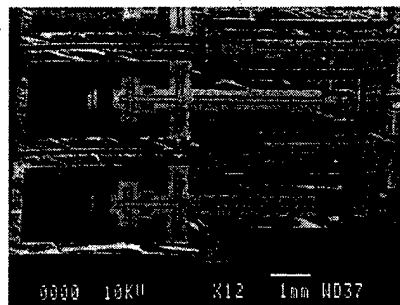


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GaAs Etched Chemistry Development

- New effort this year to micromachining GaAs structures
- Etching chemistry and masking requirements from silicon
- Initial results good for W band multiplier chips
- Additional optimization needed for thinned chips and substrateless waveguide transitions



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Project Summary

- Experimental micromachining technology developed for silicon
- Waveguide, probes, transitions and flanges developed and tested in W band
- Excellent experimental results in W band
- Nearly finished with corresponding GaAs process technology
- Technology demo with complete W band multiplier
- Ongoing efforts to use technology up to 325 GHz

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